## **AMENDMENTS TO THE CLAIMS**

## 1-13. (Cancelled)

- 14. (Currently Amended) A semiconductor device comprising:
- a semiconductor substrate having a pattern area and a non-pattern area;
- a conductor pattern formed on said pattern area of said semiconductor substrate;
- a plurality of dummy patterns formed on said non-pattern area of said semiconductor substrate:

an insulating film formed on said conductive pattern and said plurality of dummy patterns;

wherein said insulating film is formed by a chemical vapor deposition and is smoothed by chemical mechanical polishing;

wherein each of said plurality of dummy patterns are formed in a plurality of dummy areas, each of said plurality of dummy areas having a same shape, and each of said plurality of dummy patterns being arranged in a matrix with predetermined spacing;

wherein each of said dummy patterns has a space portion within each of the dummy areas so that a pattern ratio of said semiconductor device is reduced; and

wherein each of said dummy patterns includes an opening at the space portion, the opening having a shape of a letter or a number, each opening of said dummy patterns having a width less than 72  $\mu$ m; and

wherein the openings of the dummy patterns each have a shape different from one another.

15. (Previously Presented) A semiconductor device according to claim 14, wherein each of said dummy patterns has a rectangular outline.

### 16-17. (Cancelled)

18. (Currently Amended) A semiconductor device according to claim 15, wherein the

each opening has a shape of a plurality of letters.

# 19-24. (Cancelled)

25. (Previously Presented) A method of manufacturing the semiconductor device of claim 14, the method comprising:

forming the conductor pattern and the dummy patterns above the semiconductor substrate;

forming the insulating film on the conductor pattern and the dummy patterns by chemical vapor deposition, the opening of each dummy pattern being filled by the insulating film; and smoothing the insulating film by chemical mechanical polishing.

# 26-29. (Cancelled)

- 30. (Previously Presented) The method according to claim 25, wherein the insulating film is Boro Phospho Silicate Glass (BPSG) oxide film.
- 31. (Previously Presented) The method according to claim 25, wherein the insulating film is High Density Plasma-Chemical Vapor Deposition (HDP-CVD) oxide film.